MBD770DWT1G, NSVMBD770DW1T1G

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- AEC Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 150°C unless otherwise noted)

Rating	Symbol	Value	Unit
Forward Current	IF	100	mA
Non-Repetitive Peak Forward Surge Current (60 Hz Half Sine)	I _{FSM}	1	Α
Reverse Voltage	V _R	70	V
Forward Power Dissipation @ T _A = 25°C Derate above 25°C (Note 1)	P _F	380 3	mW mW/°C
Operating Junction and Storage Temperature Range	T _{J,} T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

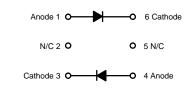
1. FR4 @ 100 mm², 1 oz Cu



ON Semiconductor®

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70 VOLTS SCHOTTKY BARRIER DIODES







SOT-363 CASE 419B STYLE 6



M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MBD770DWT1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSVMBD770DW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBD770DWT1G, NSVMBD770DW1T1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu A$)	V _{(BR)R}	70	-	V
Total Capacitance $(V_R = 20 \text{ V}, f = 1.0 \text{ MHz})$	C _T	-	1.0	pF
Reverse Leakage (V _R = 35 V)	I _R	-	200	nA
Forward Voltage (I _F = 1.0 mA)	V _F	-	500	mV
Forward Voltage (I _F = 10 mA)	V _F	_	1.0	V

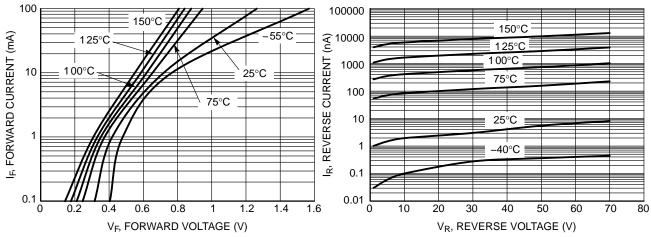


Figure 1. Typical Forward Voltage

Figure 2. Reverse Current versus Reverse Voltage

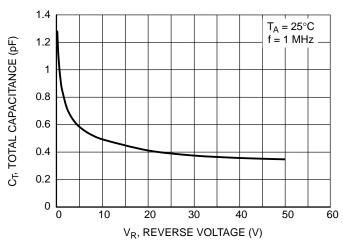


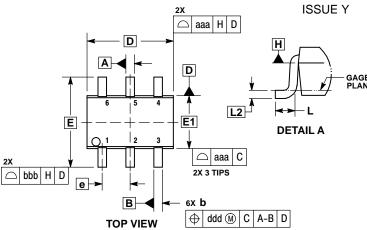
Figure 3. Typical Capacitance

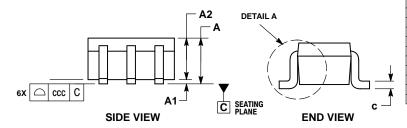
MBD770DWT1G, NSVMBD770DW1T1G

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02



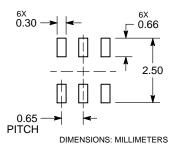


NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
- DATUMS A AND B ARE DETERMINED AT DATUM H.
 DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE
 LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION.
- ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC		0.026 BSC			
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
CCC	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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